

## NPN SILICON RF POWER TRANSISTOR

### DESCRIPTION:

The ASI UHBS15-1 is Designed for

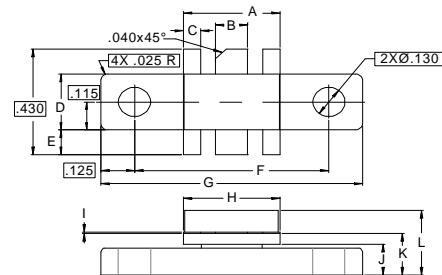
### FEATURES:

- 
- 
- **Omnigold™** Metalization System

### MAXIMUM RATINGS

$I_C$	2.0 A
$V_{CBO}$	55 V
$V_{CEO}$	28 V
$V_{CES}$	55 V
$V_{EBO}$	4.0 V
$P_{DISS}$	57.5 W @ $T_C = 25^\circ\text{C}$
$T_J$	$-65^\circ\text{C}$ to $+200^\circ\text{C}$
$T_{STG}$	$-65^\circ\text{C}$ to $+150^\circ\text{C}$
$\theta_{JC}$	$3.0^\circ\text{C/W}$

### PACKAGE STYLE .230 6L FLG



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.355 / 9.02	.365 / 9.27
B	.115 / 2.92	.125 / 3.18
C	.075 / 1.91	.085 / 2.16
D	.225 / 5.72	.235 / 5.97
E	.090 / 2.29	.110 / 2.79
F	.720 / 18.29	.730 / 18.54
G	.970 / 24.64	.980 / 24.89
H	.355 / 9.02	.365 / 9.27
I	.004 / 0.10	.006 / 0.15
J	.120 / 3.05	.130 / 3.30
K	.160 / 4.06	.180 / 4.57
L	.230 / 5.84	.260 / 6.60

**ORDER CODE: ASI10668**

### CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CES}$	$I_C = 50\text{ mA}$	55			V
$BV_{CEO}$	$I_C = 50\text{ mA}$ $R_{BE} = 10\ \Omega$	28			V
$BV_{EBO}$	$I_E = 10\text{ mA}$	4.0			V
$I_{CBO}$	$V_{CB} = 15\text{ V}$			2.5	mA
$h_{FE}$	$V_{CE} = 5.0\text{ V}$ $I_C = 1.0\text{ A}$	20	---	---	---
$C_{ob}$	$V_{CB} = 24\text{ V}$ $f = 1.0\text{ MHz}$			25	pF
$P_G$ $\eta_c$	$V_{CC} = 24\text{ V}$ $P_{OUT} = 15\text{ W}$ $f = 900\text{ GHz}$	9.5	55		dB %